TOSHIBA Field Effect Transistor Silicon N Channel Junction Type

2SK211

FM Tuner Applications VHF Band Amplifier Applications

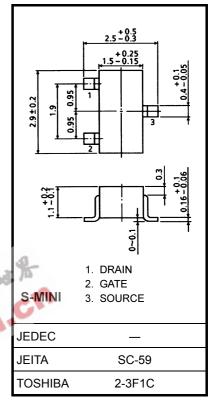
- Low noise figure: NF = 2.5 dB (typ.) (f = 100 MHz)
- High forward transfer admitance: $|Y_{fs}| = 9 \text{ mS}$ (typ.)
- Extremely low reverse transfer capacitance: $C_{rss} = 0.1 \text{ pF}$ (typ.)

Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Gate-drain voltage	V _{GDO}	-18	V
Gate current	IG	10	mA
Drain power dissipation	PD	150	mW
Junction temperature	Тj	125	°C
Storage temperature range	T _{stg}	-55~125	°C

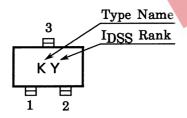
Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).



Weight: 0.012 g (typ.)

Marking

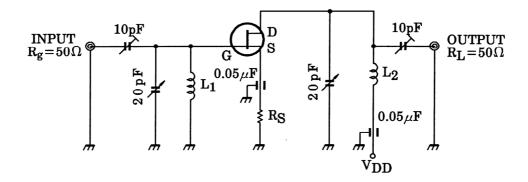


Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	$V_{GS} = -0.5 \text{ V}, V_{DS} = 0 \text{ V}$	—	—	-10	nA
Gate-drain breakdown voltage	V (BR) GDO	$I_G = -100 \ \mu A$	-18	_	—	V
Drain current	I _{DSS} (Note)	$V_{GS} = 0 V, V_{DS} = 10 V$	1.0	_	10	mA
Gate-source cut-off voltage	V _{GS (OFF)}	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 1 \mu\text{A}$	-0.4	_	-4.0	V
Forward transfer admittance	Y _{fs}	$V_{GS} = 0 V, V_{DS} = 10 V, f = 1 kHz$	_	9		mS
Input capacitance	C _{iss}	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		6.0		pF
Reverse transfer capacitance	C _{rss}	$V_{GD} = -10 V, f = 1 MHz$			0.15	pF
Power gain	G _{PS}	V _{DD} = 10 V, f = 100 MHz (Figure)		18		dB
Noise figure	NF	V _{DD} = 10 V, f = 100 MHz (Figure)	_	2.5	3.5	dB

Note: I_{DSS} classification O: 1.0~3.0 mA, Y: 2.5~6.0 mA, GR (G): 5.0~10.0 mA

Unit: mm



L₁: 0.8 mm ϕ Ag PLATED Cu WIRE 3 TURNS, 10 mm ID, 10 mm LENGTH L₂: 0.8 mm ϕ Ag PLATED Cu WIRE 3.5 TURNS, 10 mm ID, 10 mm LENGTH

Figure 100 MHz G_{PS}, NF Test Circuit

Group	RS (Ω)	
2SK211-O	0	
2SK211-Y	$18~\Omega\pm5\%$	
2SK211-GR	100 $\Omega\pm5\%$	

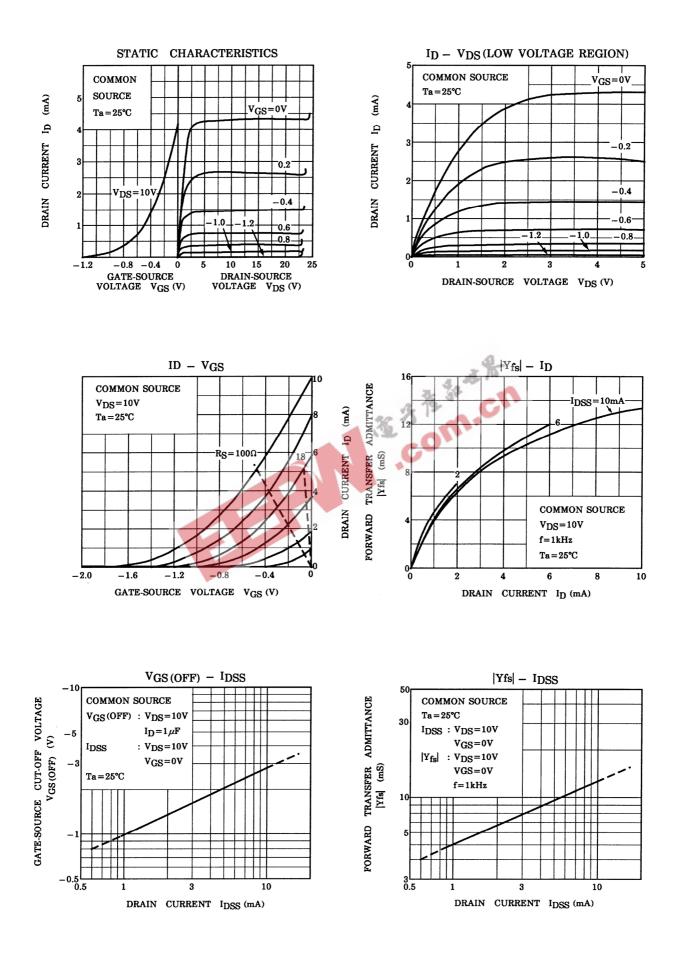
2SK211 is measured at each group by changing $R_{\rm s}.$

 RS (Ω)

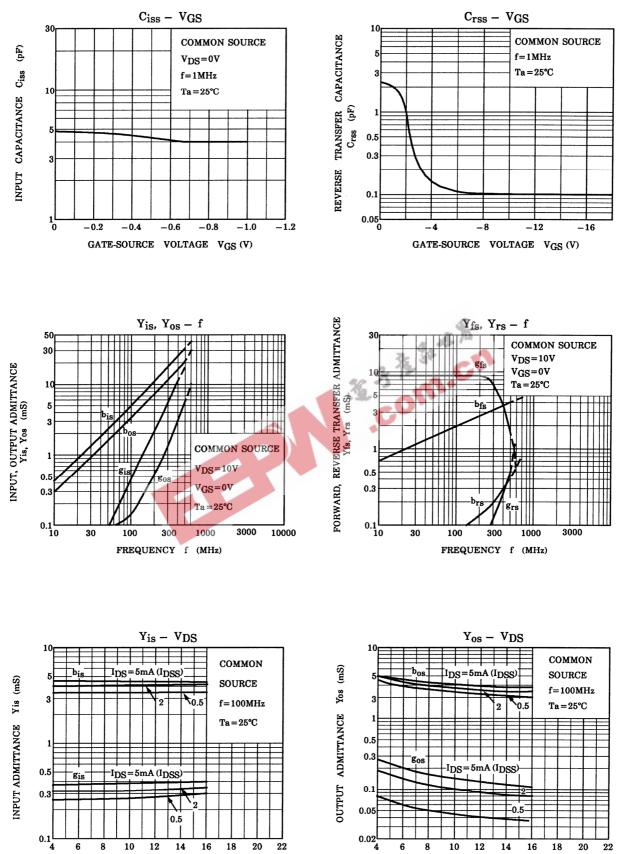
 0

 18 Ω ± 5%

 100 Ω ± 5%

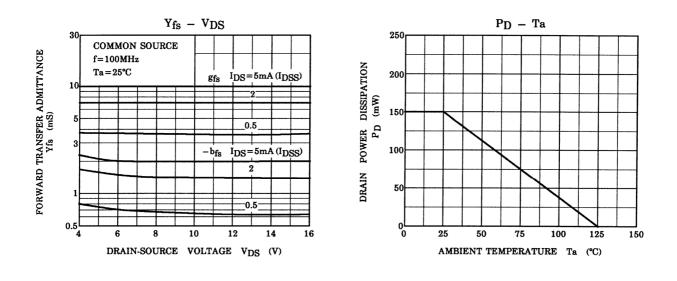


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DRAIN-SOURCE VOLTAGE $V_{DS}(V)$

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20070701-EN GENERAL

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